



4N65-C

Power MOSFET

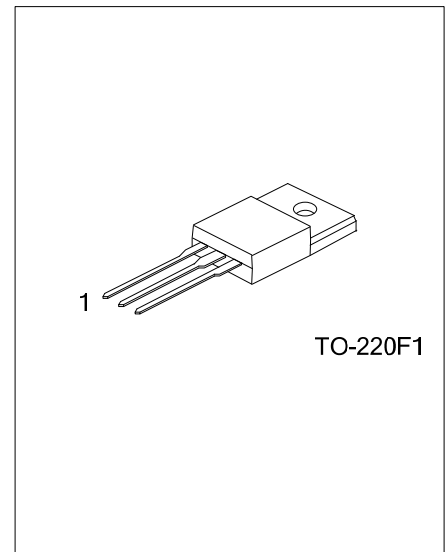
4A, 650V N-CHANNEL POWER MOSFET

DESCRIPTION

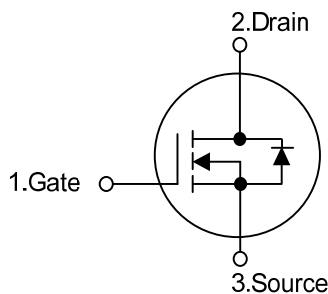
The UTC **4N65-C** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 3.0\Omega$ @ $V_{GS} = 10V, I_D = 2A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



SYMBOL



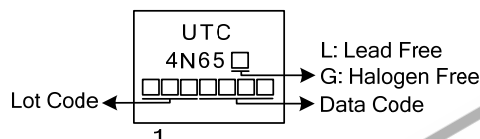
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N65L-TF1-T	4N65G-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N65L-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current (Note2)	I_{AR}	4.0	A
Drain Current	Continuous	I_D	4.0
	Pulsed (Note2)	I_{DM}	16
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	150
	Repetitive (Note2)	E_{AR}	5.6
Peak Diode Recovery dv/dt (Note4)	dv/dt	3.6	V/ns
Power Dissipation	P_D	36	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 18.75\text{mH}$, $I_{AS} = 4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	3.47	$^\circ\text{C}/\text{W}$

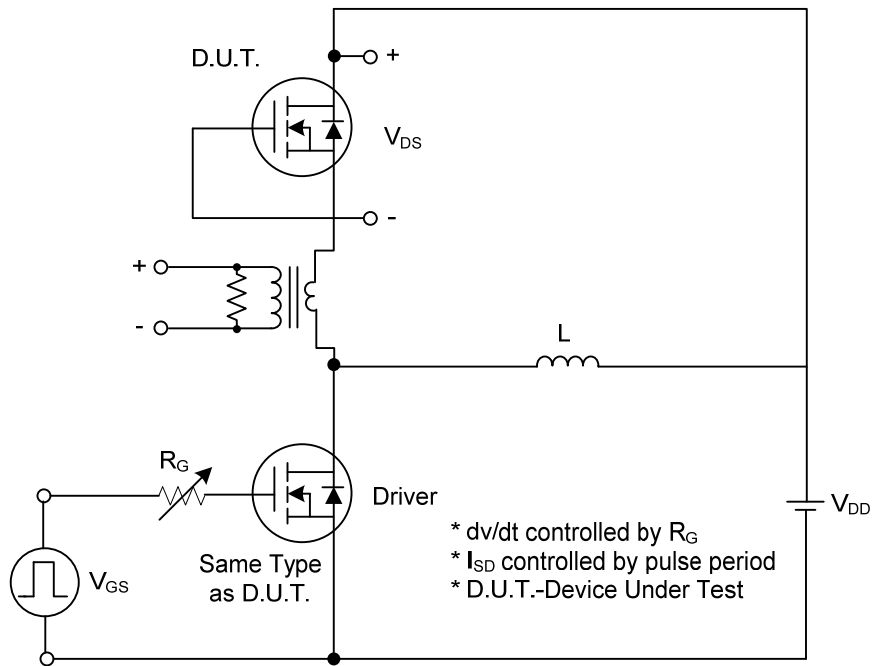
■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			10	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$			100	μA
Gate-Source Leakage Current	Forward	I_{GSS}				nA
	Reverse					
		$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$			3.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		425		pF
Output Capacitance	C_{OSS}			55		pF
Reverse Transfer Capacitance	C_{RSS}			5.8		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS} = 50\text{ V}, I_D = 1.3\text{ A}, I_G = 100\mu\text{A}$ $V_{GS} = 10\text{ V}$ (Note 1, 2)		16.5		nC
Gate-Source Charge	Q_{GS}			4		nC
Gate-Drain Charge	Q_{GD}			3.4		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DS} = 30\text{ V}, I_D = 0.5\text{ A}, R_G = 25\Omega$ (Note 1, 2)		37		ns
Turn-On Rise Time	t_R			33		ns
Turn-Off Delay Time	$t_{D(OFF)}$			45		ns
Turn-Off Fall Time	t_F			40		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 4.0\text{ A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				4.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				16	A
Body Diode Reverse Recovery Time	t_{RR}	$I_F = 4.0\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		320		ns
Body Diode Reverse Recovery Charge	Q_{RR}			2.0		nC

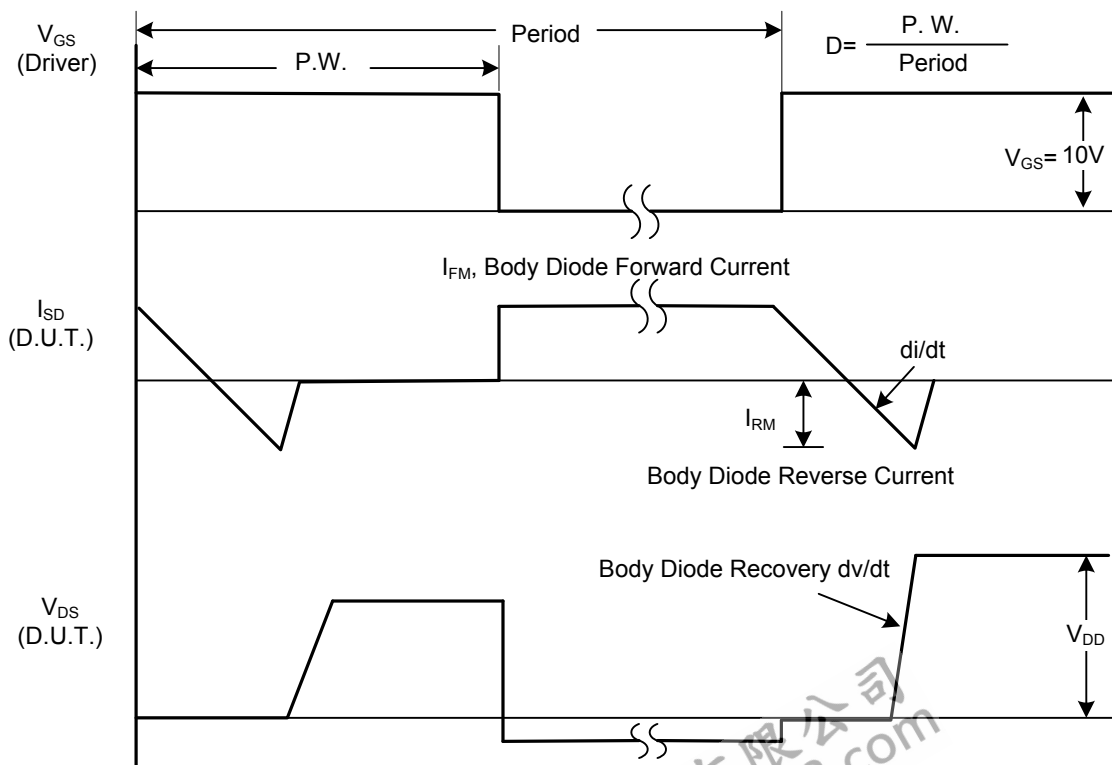
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

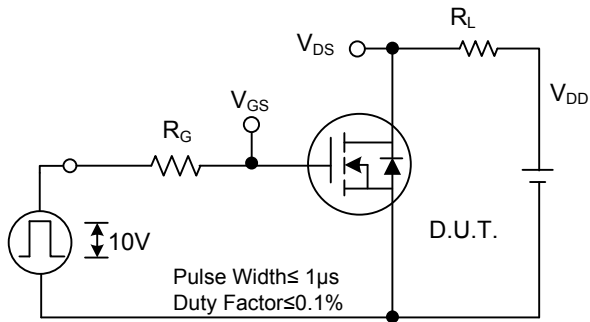


Peak Diode Recovery dv/dt Test Circuit

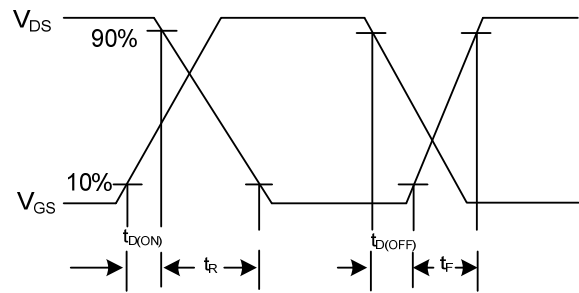


Peak Diode Recovery dv/dt Waveforms

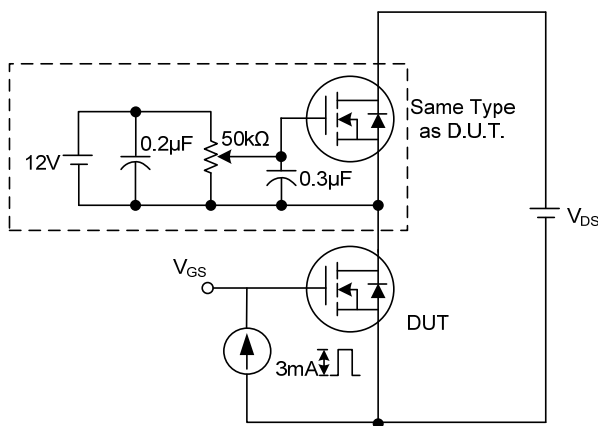
TEST CIRCUITS AND WAVEFORMS (Cont.)



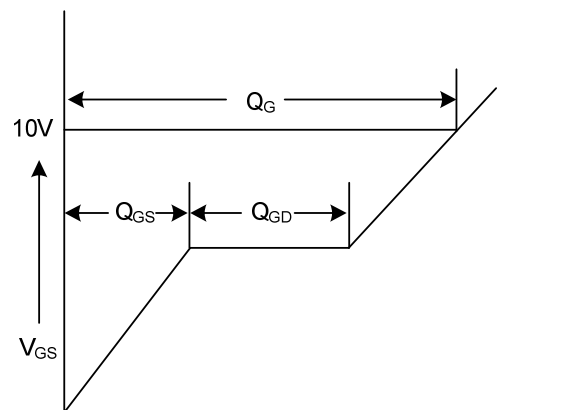
Switching Test Circuit



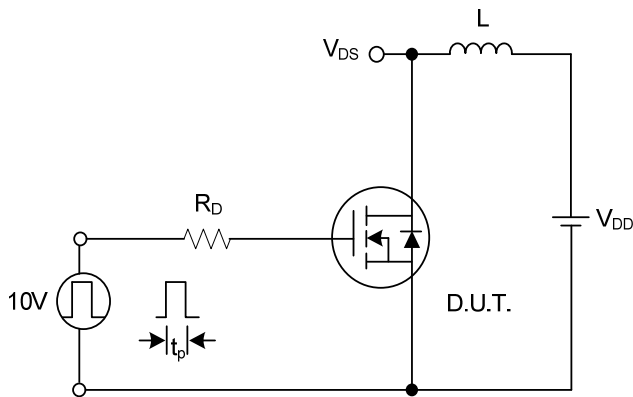
Switching Waveforms



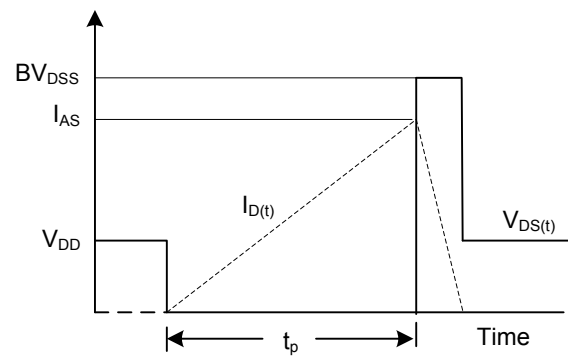
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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